

Type Designator: BLY17

Material of Transistor: Si

Polarity: NPN

Maximum Collector Power Dissipation ( $P_c$ ): 100 W

Maximum Collector-Base Voltage  $|V_{cb}|$ : 100 V

Maximum Collector-Emitter Voltage  $|V_{ce}|$ : 50 V

Maximum Emitter-Base Voltage  $|V_{eb}|$ : 4 V

Maximum Collector Current  $|I_c \text{ max}|$ : 10 A

Max. Operating Junction Temperature ( $T_j$ ): 200 °C

Transition Frequency ( $f_t$ ): 35 MHz

Forward Current Transfer Ratio ( $h_{FE}$ ), MIN: 5

Noise Figure, dB: -

Package: TO36